

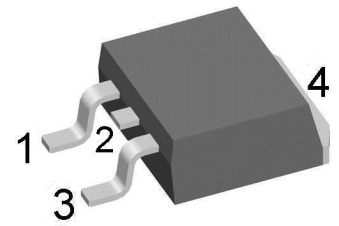
**HiPerFRED**

$V_{RRM}$	=	300 V
$I_{FAV}$	=	40 A
$t_{rr}$	=	35 ns

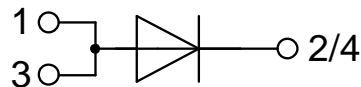
High Performance Fast Recovery Diode  
 Low Loss and Soft Recovery  
 Single Diode

Part number

**DSEP40-03AS**



Backside: cathode

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

**Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

**Package:** TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

**Terms .Conditions of usage:**

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

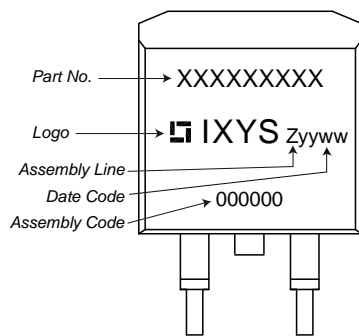
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage				300	V	
$V_{RRM}$	max. repetitive reverse blocking voltage				300	V	
$I_R$	reverse current, drain current	$V_R = 300\text{ V}$			5	$\mu\text{A}$	
		$V_R = 300\text{ V}$			0.1	mA	
$V_F$	forward voltage drop	$I_F = 40\text{ A}$			1.46	V	
		$I_F = 80\text{ A}$			1.85	V	
		$I_F = 40\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.20	V
		$I_F = 80\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.63	V
$I_{FAV}$	average forward current	$T_C = 120^\circ\text{C}$ rectangular $d = 0.5$			40	A	
$V_{FO}$	threshold voltage	} for power loss calculation only			0.72	V	
$r_F$	slope resistance				10.7	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				0.85	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W	
$P_{tot}$	total power dissipation				175	W	
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$			340	A	
$C_J$	junction capacitance	$V_R = 150\text{ V}$ $f = 1\text{ MHz}$			50	pF	
$I_{RM}$	max. reverse recovery current	} $I_F = 30\text{ A}; V_R = 200\text{ V}$			3.5	A	
					7	A	
$t_{rr}$	reverse recovery time	} $-di_F/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$		35	ns	
			$T_{VJ} = 125^\circ\text{C}$		55	ns	

Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal <sup>1)</sup>			35	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				2		g
$F_C$	mounting force with clip		20		60	N

<sup>1)</sup>  $I_{RMS}$  is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

### Product Marking

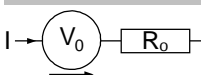


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP40-03AS	DSEP40-03AS	Tape & Reel	800	501174

### Equivalent Circuits for Simulation

\* on die level

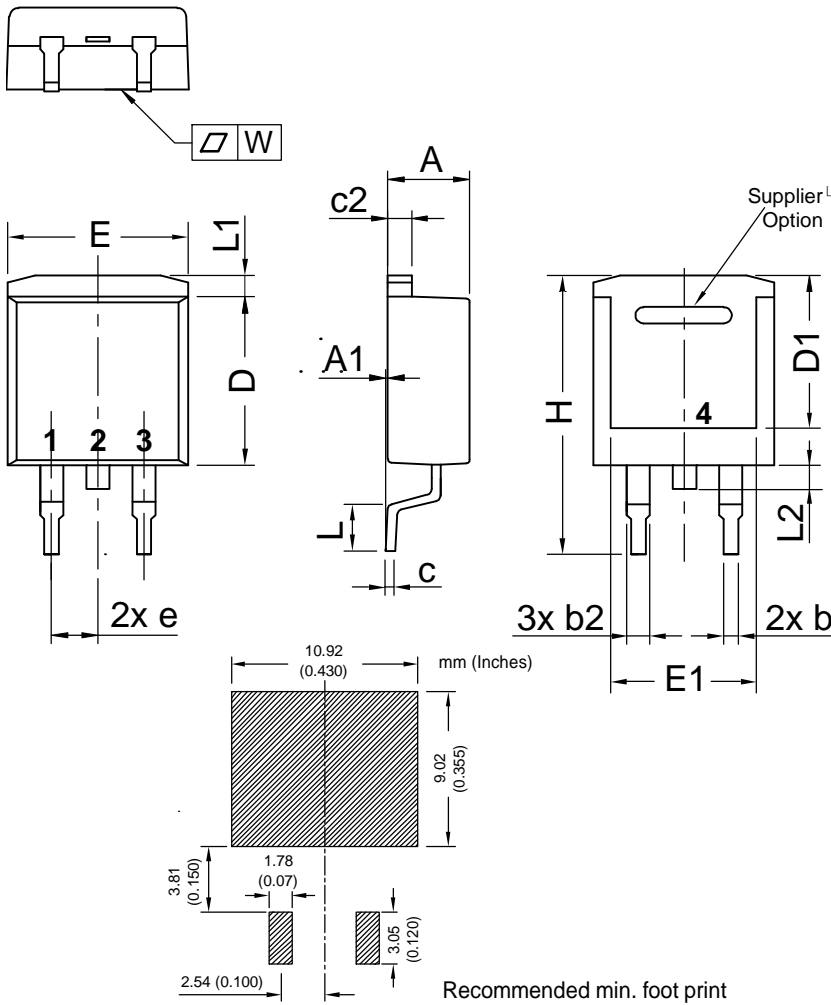
$T_{VJ} = 175\text{ °C}$



**Fast Diode**

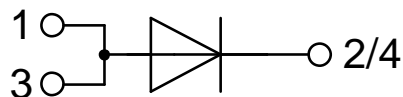
$V_{0\ max}$	threshold voltage	0.72	V
$R_{0\ max}$	slope resistance *	7.5	mΩ

## Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

*All dimensions conform with and/or within JEDEC standard.*



## Fast Diode

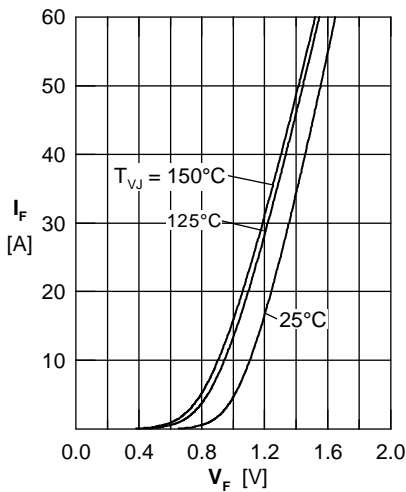


Fig. 1 Forward current  $I_F$  versus forward voltage  $V_F$

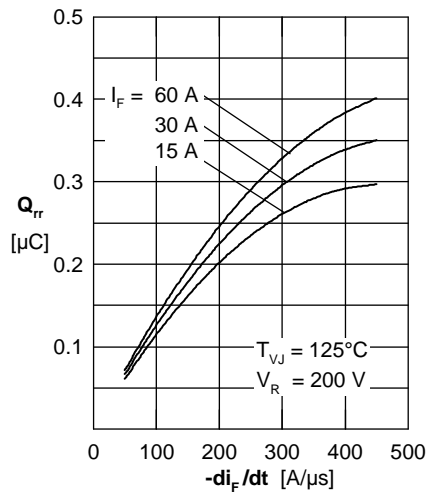


Fig. 2 Typ. reverse recovery charge  $Q_{rr}$  versus  $-di_F/dt$

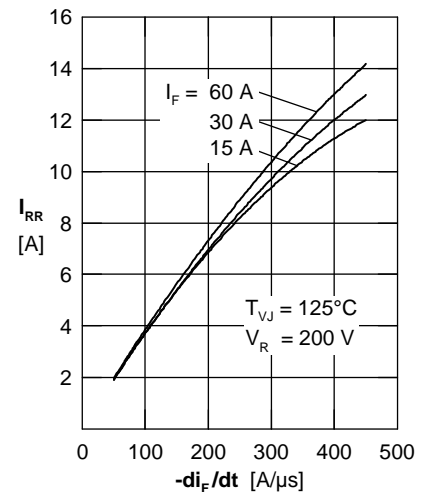


Fig. 3 Typ. reverse recovery current  $I_{RR}$  versus  $-di_F/dt$

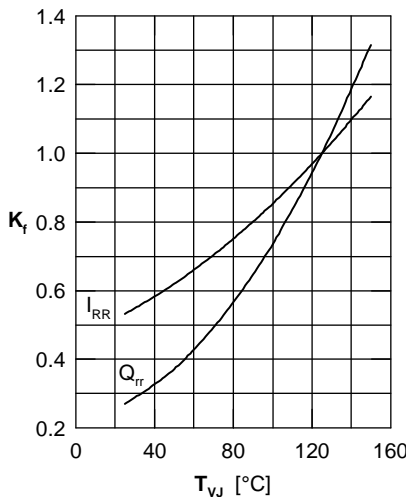


Fig. 4 Dynamic parameters  $Q_{rr}$ ,  $I_{RR}$  versus  $T_{VJ}$

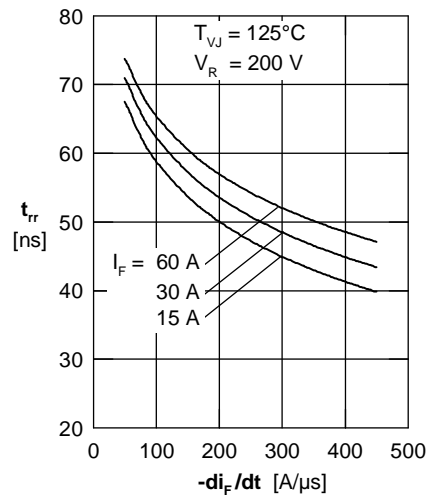


Fig. 5 Typ. reverse recovery time  $t_{rr}$  versus  $-di_F/dt$

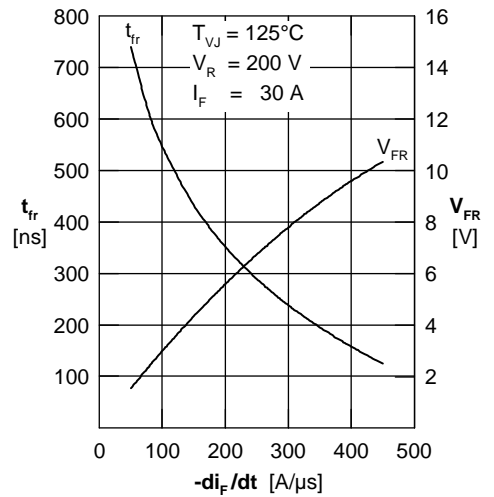


Fig. 6 Typ. forward recovery voltage  $V_{FR}$  & forward recovery time  $t_{fr}$  vs.  $di_F/dt$

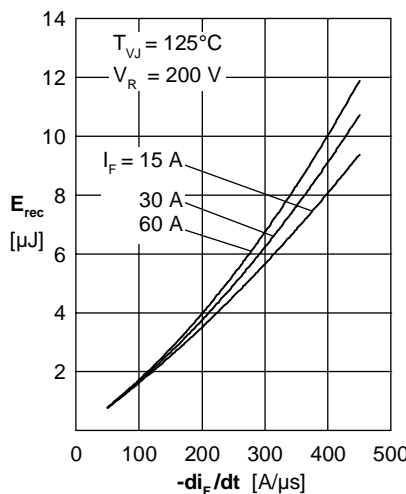


Fig. 7 Typ. recovery energy  $E_{rec}$  versus  $-di_F/dt$

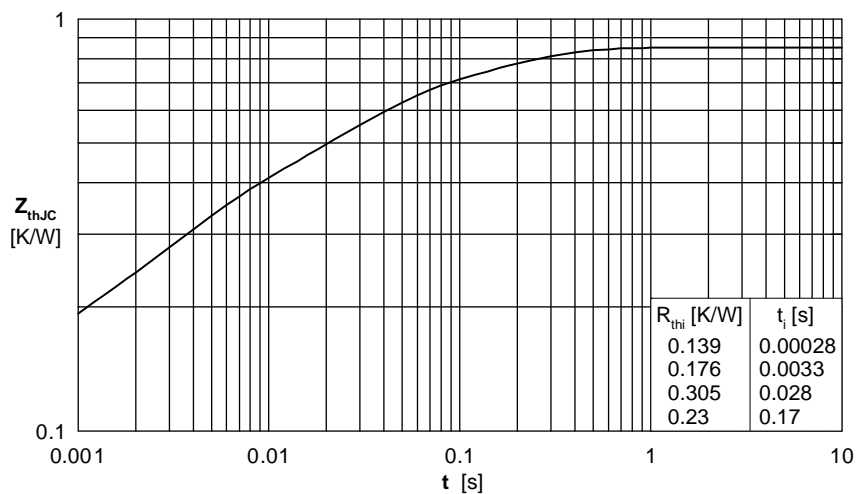


Fig. 8 Transient thermal impedance junction to case